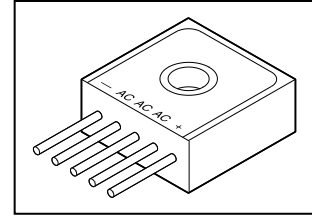


TECHNICAL DATA
DATA SHEET 757, REV. C

**THREE PHASE FULL WAVE
BRIDGE RECTIFIER ASSEMBLY**



DESCRIPTION: A 1000 VOLT, 30 AMP, 5000 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

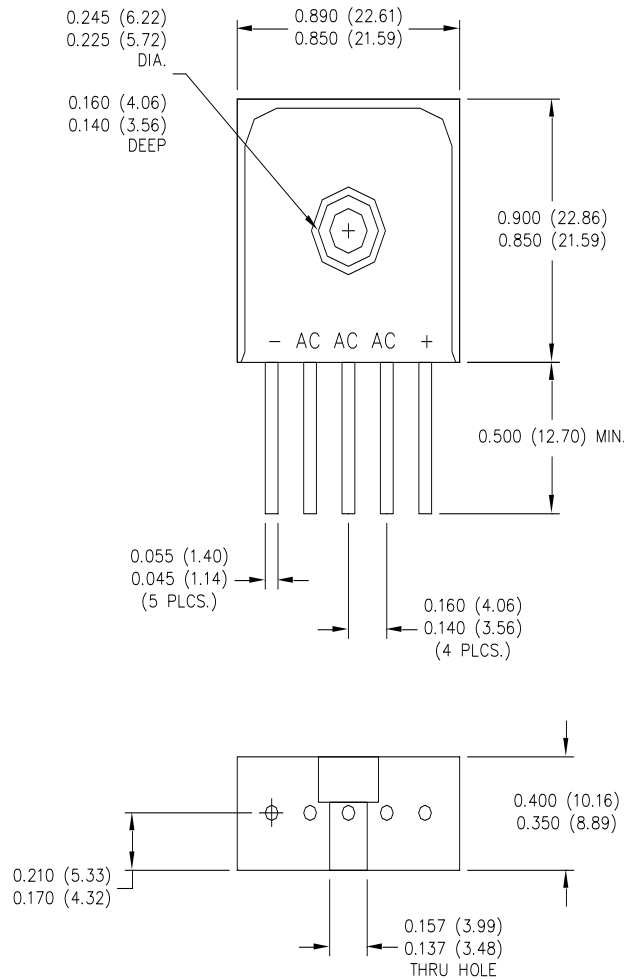
MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-	1000	Vdc
Average DC Output Current ($T_C = \text{Case Temp}$) (I_o)	$T_C = 55^\circ\text{C}$ $T_C = 100^\circ\text{C}$	-	-	30 20	Amps
Peak Single Cycle Surge Current (I_{FSM})	$t_p = 8.3 \text{ ms}$ Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	100	Amps(pk)
Peak Recurring Surge Current (I_{FRM})	$T_A = 25^\circ\text{C}$	-	-	35	Amps
Operating and Storage Temp. (T_{op} & T_{stg})	-	-55	-	+150	$^\circ\text{C}$
Maximum Forward Voltage Per Leg (V_f)	$I_f = 9.0\text{A}$ dc (300 μsec pulse, duty cycle < 2%)	-	-	1.4	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	5.0 100	μAmps
Reverse Recovery Time (t_{rr})	$I_f = 0.5\text{A}$, $I_r = 1.0\text{A}$; $I_{rr} =$ 0.25A Measured on discrete rectifiers prior to assembly.	-	-	5000	nsec
Max. Thermal Resistance ($R\theta_{JC}$)	-	-	-	1.50	$^\circ\text{C/W}$

MECHANICAL DIMENSIONS: In Inches / mm

Fig. 455

Note: Case finish - Black Anodized



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